



**THE DATASHEET OF
TAS5176DDW6EVM**



6-Channel, 100-W, Digital-Amplifier Power Stage

FEATURES

- **Total Output Power at 10% THD+N**
 - 5 × 15 W at 8 Ω + 1 × 25 W at 4 Ω (Single-Ended)
 - 2 × 30 W at 8 Ω (BTL)
 - 1 × 40 W at 6 Ω (BTL)
- **105-dB SNR (A-Weighted), with TAS5086 Modulator**
- **< 0.05% THD+N at 1 W**
- **Power Stage Efficiency > 90% Into Recommended Loads (SE)**
- **Integrated Self-Protection Circuits**
 - Undervoltage
 - Overtemperature
 - Overload
 - Short Circuit
- **Integrated Active-Bias Control to Avoid DC Pop**
- **Footprint Compatible with the TAS5186A for Scaleable Designs**
- **Thermally Enhanced 44-pin HTSSOP Package with PowerPad located on the bottom of the device**
- **EMI-Compliant When Used With Recommended System Design**

APPLICATIONS

- DVD Receiver
- Home Theater in a Box
- Televisions

DESCRIPTION

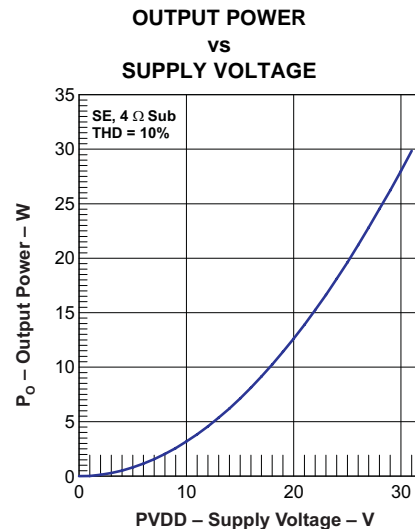
The TAS5176 is a high-performance, six-channel, digital-amplifier power stage with an improved protection system. The TAS5176 is capable of driving a 8-Ω, single-ended load up to 15 W per each front/satellite channel and a 4-Ω, single-ended subwoofer greater than 25 W at 10% THD+N performance.

Furthermore, the TAS5176 can drive three-channels in BTL mode, with the same high-performance but with a higher power level. In BTL mode, the TAS5176 is capable of driving 8-Ω loads to greater than 30 Watts at 10% THD+N performance.

A low-cost, high-fidelity audio system can be built using a TI chipset comprising a modulator (e.g., TAS5086) and the TAS5176. This device does not require power-up sequencing because of the internal power-on reset.

The TAS5176 requires only simple passive demodulation filters on its outputs to deliver high-quality, high-efficiency audio amplification. The efficiency of the TAS5176 is greater than 90% when driving 8-Ω satellites and a 4-Ω subwoofer speaker.

The TAS5176 has an innovative protection system integrated on-chip, safeguarding the device against a wide range of fault conditions that could damage the system. These safeguards are short-circuit protection, overload protection, undervoltage protection, and overtemperature protection. The TAS5176 has a new proprietary current-limiting circuit that reduces the possibility of device shutdown during high-level music transients. A new programmable overcurrent detector allows the use of lower-cost inductors in the demodulation output filter.



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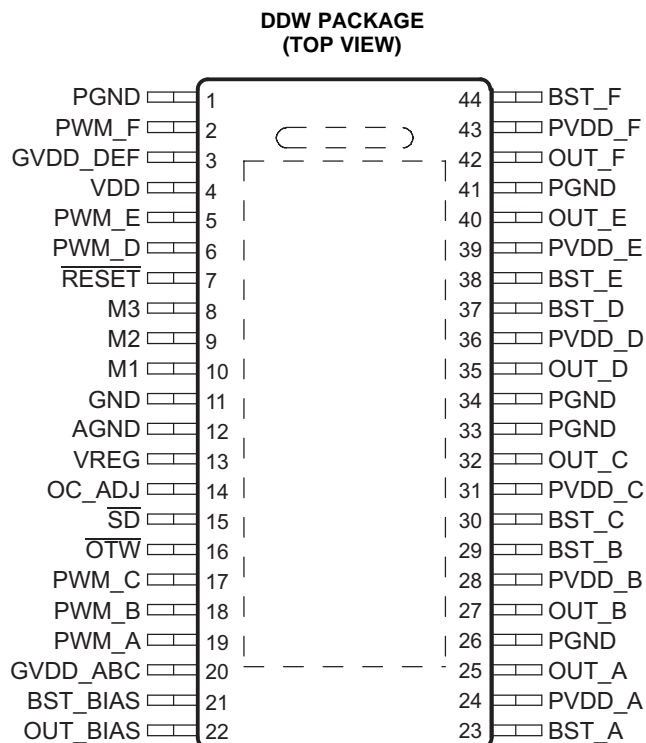


These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

DEVICE INFORMATION

TERMINAL ASSIGNMENT

The TAS5176 is available in a thermally enhanced 44-pin HTSSOP PowerPAD™ package. The heat slug is located on the bottom side of the device for convenient thermal coupling to the printed circuit board which is used as the heatsink for this device.



P0016-02

DEVICE INFORMATION (continued)
TERMINAL FUNCTIONS

| TERMINAL | | TYPE (1) | DESCRIPTION |
|----------|-------------------------------|----------|--|
| NAME | NO. | | |
| AGND | 12 | P | Analog ground |
| BST_A | 23 | P | HS bootstrap supply (BST), capacitor to OUT_A required |
| BST_B | 29 | P | HS bootstrap supply (BST), external capacitor to OUT_B required |
| BST_BIAS | 21 | P | BIAS bootstrap supply, external capacitor to OUT_BIAS required |
| BST_C | 30 | P | HS bootstrap supply (BST), external capacitor to OUT_C required |
| BST_D | 37 | P | HS bootstrap supply (BST), external capacitor to OUT_D required |
| BST_E | 38 | P | HS bootstrap supply (BST), external capacitor to OUT_E required |
| BST_F | 44 | P | HS bootstrap supply (BST), external capacitor to OUT_F required |
| GND | 11 | P | Chip ground |
| GVDD_ABC | 20 | P | Gate drive voltage supply |
| GVDD_DEF | 3 | P | Gate drive voltage supply |
| M1 | 10 | I | Mode selection pin |
| M2 | 9 | I | Mode selection pin |
| M3 | 8 | I | Mode selection pin |
| OC_ADJ | 14 | O | Overcurrent threshold programming pin, resistor to AGND required |
| OTW | 16 | O | Overtemperature warning open-drain output signal, active-low |
| OUT_A | 25 | O | Output, half-bridge A, satellite |
| OUT_B | 27 | O | Output, half-bridge B, satellite |
| OUT_BIAS | 22 | O | BIAS half-bridge output pin |
| OUT_C | 32 | O | Output, half-bridge C, subwoofer |
| OUT_D | 35 | O | Output, half-bridge D, satellite |
| OUT_E | 40 | O | Output, half-bridge E, satellite |
| OUT_F | 42 | O | Output, half-bridge F, satellite |
| PGND | 1, 26, 33, 34, 41 | P | Power ground |
| PVDD_A | 24 | P | Power-supply input for half-bridge A |
| PVDD_B | 28 | P | Power-supply input for half-bridge B |
| PVDD_C | 31 | P | Power-supply input for half-bridge C |
| PVDD_D | 36 | P | Power-supply input for half-bridge D |
| PVDD_E | 39 | P | Power-supply input for half-bridge E |
| PVDD_F | 43 | P | Power-supply input for half-bridge F |
| PWM_A | 19 | I | PWM input signal for half-bridge A |
| PWM_B | 18 | I | PWM input signal for half-bridge B |
| PWM_C | 17 | I | PWM input signal for half-bridge C |
| PWM_D | 6 | I | PWM input signal for half-bridge D |
| PWM_E | 5 | I | PWM input signal for half-bridge E |
| PWM_F | 2 | I | PWM input signal for half-bridge F |
| RESET | 7 | I | Reset signal (active-low logic) |
| SD | 15 | O | Shutdown open-drain output signal, active-low |
| VDD | 4 | P | Power supply for digital voltage regulator |
| VREG | 13 | O | Digital regulator supply filter pin, output |

(1) I = input; O = output; P = power

Table 1. MODE Selection Pins

| MODE PINS ⁽¹⁾ | | MODE | |
|--------------------------|----|----------|---|
| M2 | M3 | NAME | DESCRIPTION |
| 0 | 0 | 2.1 mode | Channels A, B, and C enabled; channels D, E, and F disabled |
| 0 | 1 | 5.1 mode | All channels enabled |
| 1 | 0 | 3.0 mode | BTL Mode |
| 1 | 1 | Reserved | |

(1) M1 must always be connected to ground. 0 indicates a pin connected to GND; 1 indicates a pin connected to VREG.

PACKAGE HEAT DISSIPATION RATINGS⁽¹⁾

| PARAMETER | TAS5176DDW |
|---|-----------------------|
| $R_{\theta JC}$ (°C/W)—1 satellite (sat.) FET only | 10.3 |
| $R_{\theta JC}$ (°C/W)—1 subwoofer (sub.) FET only | 5.2 |
| $R_{\theta JC}$ (°C/W)—1 sat. half-bridge | 5.2 |
| $R_{\theta JC}$ (°C/W)—1 sub. half-bridge | 2.6 |
| $R_{\theta JC}$ (°C/W)—5 sat. half-bridges + 1 sub. | 1.74 |
| Typical pad area ⁽²⁾ | 24.72 mm ² |

(1) JC is junction-to-case, CH is case-to-heatsink.

(2) $R_{\theta CH}$ is an important consideration. Assume a 2-mil thickness of typical thermal grease between the pad area and the heatsink. The $R_{\theta CH}$ with this condition is typically 2°C/W for this package.

ABSOLUTE MAXIMUM RATINGS

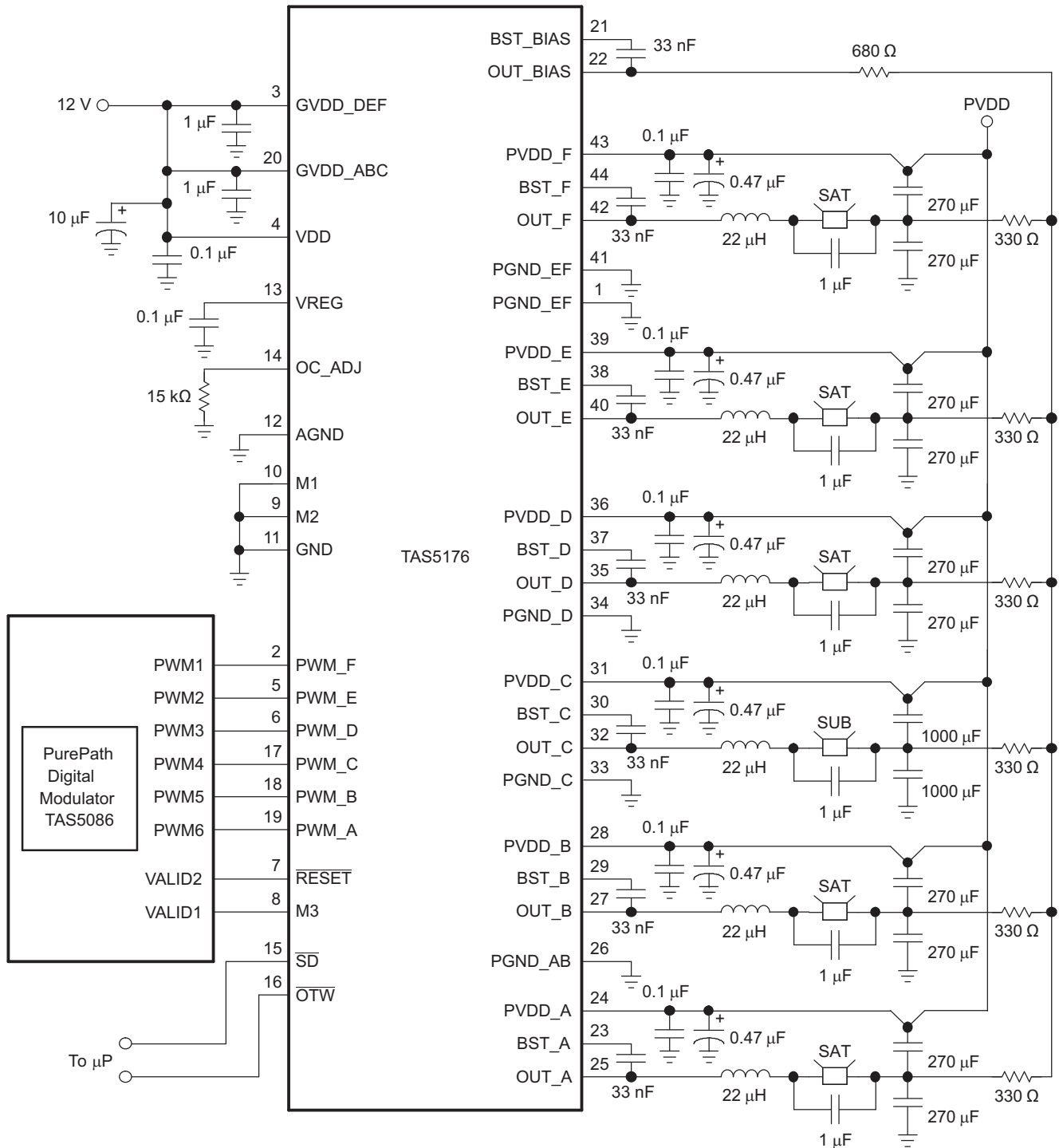
over operating free-air temperature range (unless otherwise noted)⁽¹⁾

| | UNITS |
|--|------------------|
| VDD to AGND | –0.3 V to 13.2 V |
| GVDD_X to AGND | –0.3 V to 13.2 V |
| PVDD_X to PGND_X ⁽²⁾ | –0.3 V to 50 V |
| OUT_X to PGND_X ⁽²⁾ | –0.3 V to 50 V |
| BST_X to PGND_X ⁽²⁾ | –0.3 V to 63.2 V |
| VREG to AGND | –0.3 V to 4.2 V |
| PGND_X to GND | –0.3 V to 0.3 V |
| PGND_X to AGND | –0.3 V to 0.3 V |
| GND to AGND | –0.3 V to 0.3 V |
| PWM_X, OC_ADJ, M1, M2, M3 to AGND | –0.3 V to 4.2 V |
| RESET, \overline{SD} , \overline{OTW} to AGND | –0.3 V to 7 V |
| Maximum operating junction temperature range (T_J) | 0 to 125°C |
| Storage temperature | –40°C to 125°C |
| Lead temperature – 1.6 mm (1/16 inch) from case for 10 seconds | 260°C |
| Minimum PWM pulse duration, low | 30 ns |

(1) Stresses beyond those listed under *absolute maximum ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

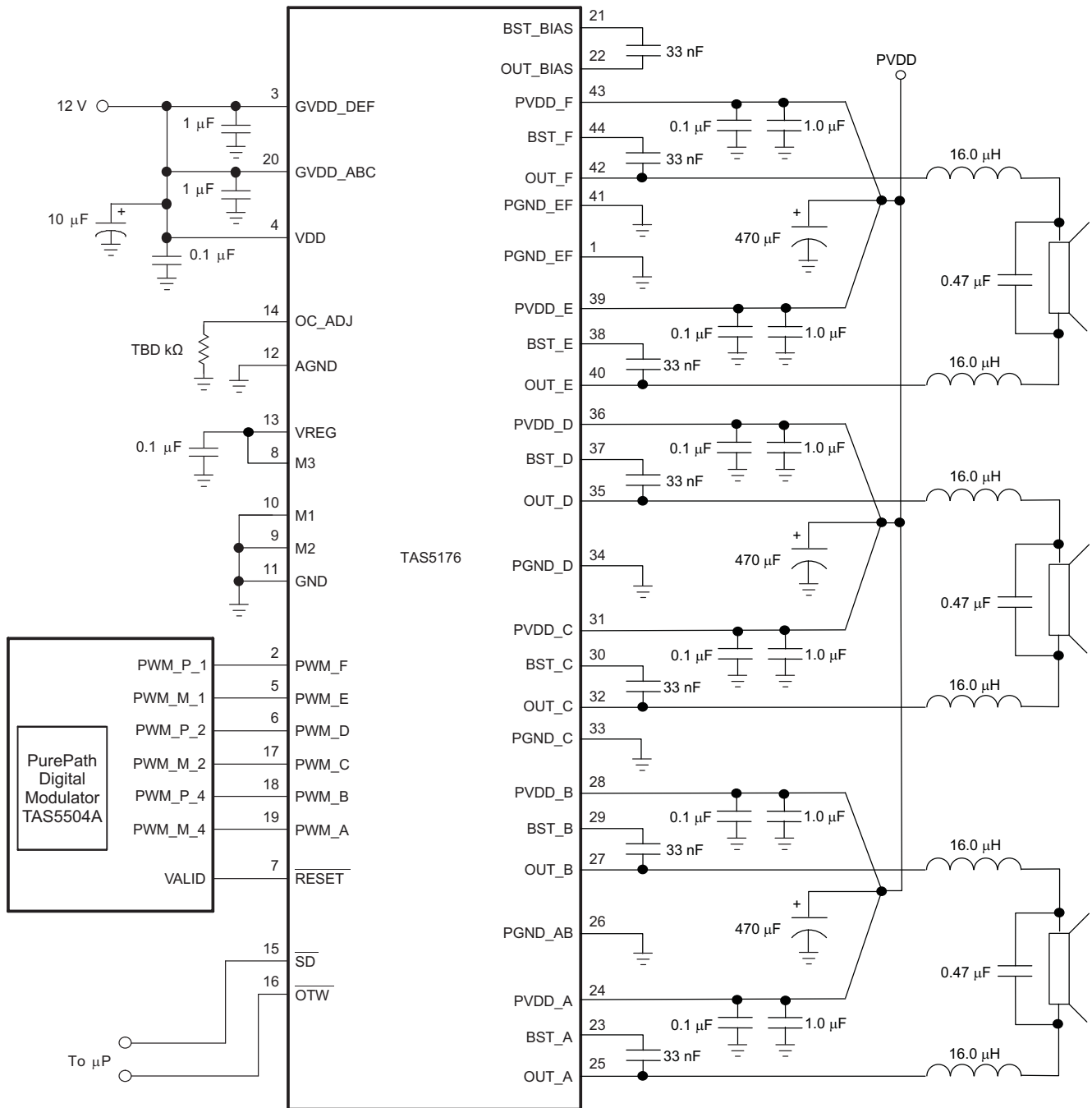
(2) These voltages represent the dc voltage + peak ac waveform measured at the terminal of the device in all conditions.

TYPICAL SYSTEM DIAGRAM (Single-ended Mode)

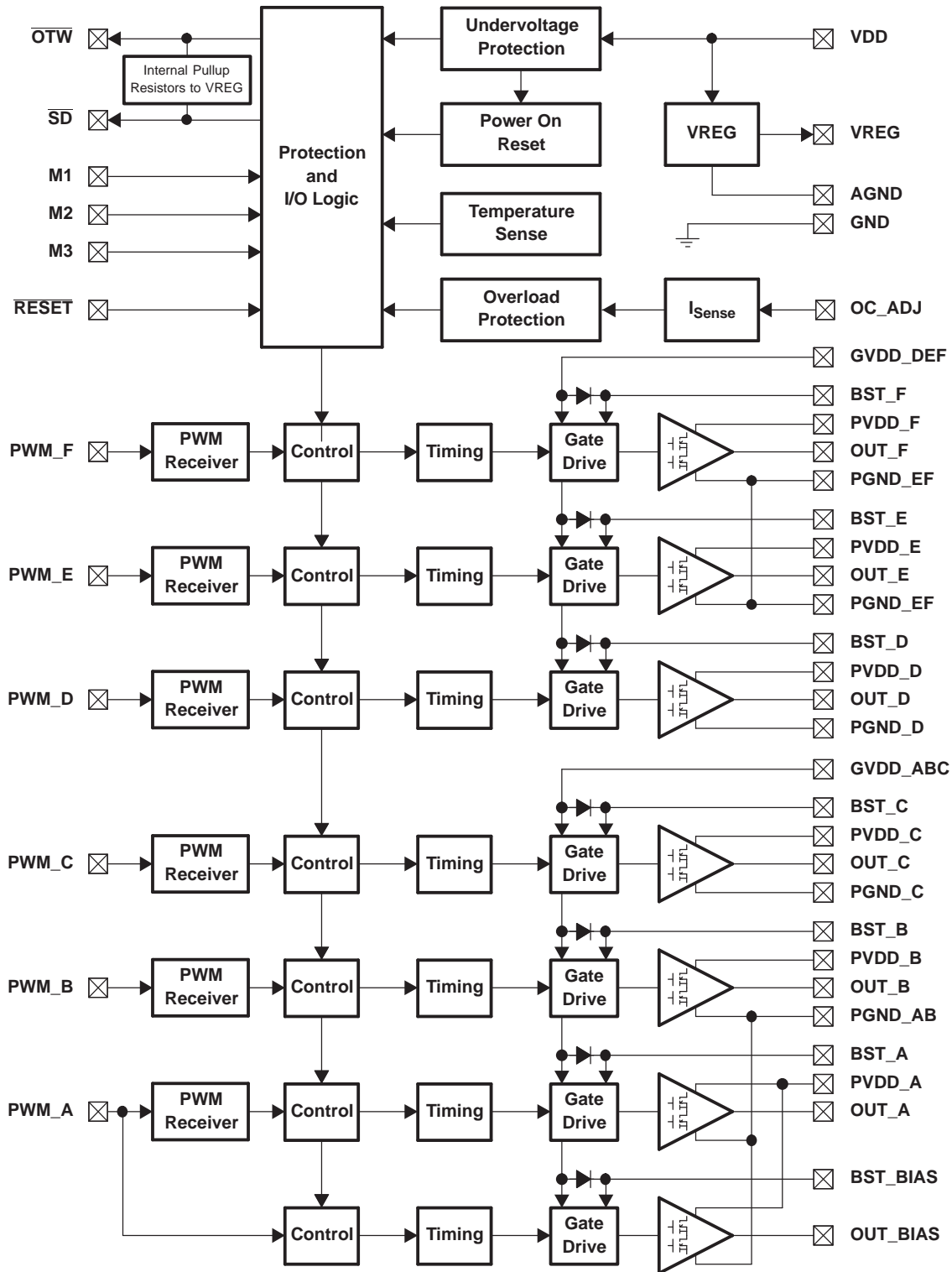


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TYPICAL SYSTEM DIAGRAM (BTL Mode)



FUNCTIONAL BLOCK DIAGRAM



B0034-01

RECOMMENDED OPERATING CONDITIONS

| | | | MIN | TYP | MAX | UNIT |
|-------------------------|---|---|------|-----|------|------|
| PVDD_X | Half-bridge supply, SE | DC supply voltage at pin(s) | 0 | 31 | 34 | V |
| GVDD | Gate drive and guard ring supply voltage | DC voltage at pin(s) | 10.8 | 12 | 13.2 | V |
| VDD | Digital regulator supply | DC supply voltage at pin | 10.8 | 12 | 13.2 | V |
| R _{L,SAT} | Resistive load impedance, satellite channels ⁽¹⁾ | Recommended demodulation filter | 6 | 8 | | Ω |
| R _{L,SUB} | Resistive load impedance, subwoofer channel | Recommended demodulation filter | 3.5 | 4 | | Ω |
| L _{output} | Demodulation filter inductance | Minimum output inductance under short-circuit condition | 5 | 22 | | μH |
| C _{output,sat} | Demodulation filter capacitance | | | 1 | | μF |
| C _{output,sub} | Demodulation filter capacitance | | | 1 | | μF |
| F _{PWM} | PWM frame rate | | 192 | 384 | 432 | kHz |

(1) Load impedance outside range listed might cause shutdown due to OLP, OTE, or NLP.

AUDIO SPECIFICATION (Single-Ended Operation)

PVDD_X = 31 V, GVDD = 12 V, audio frequency = 1 kHz, AES17 measurement filter, F_{PWM} = 384 kHz, case temperature = 75°C. Audio performance is recorded as a chipset, using TAS5086 PWM processor with an effective modulation index limit of 97%. All performance is in accordance with the foregoing specifications and recommended operating conditions unless otherwise specified.

| PARAMETER | | CONDITIONS | MIN | TYP | MAX | UNIT |
|--------------------|---|--|-----|-----|-----|------|
| P _{O,sat} | Power output per satellite channel | R _L = 8 Ω, 10% THD, clipped input signal | | 15 | | W |
| | | R _L = 8 Ω, 0 dBFS, unclipped input signal | | 12 | | |
| P _{O,sub} | Power output, subwoofer | R _L = 4 Ω, 10% THD, clipped input signal | | 25 | | W |
| | | R _L = 4 Ω, 0 dBFS, unclipped input signal | | 22 | | |
| THD + N | Total harmonic distortion + noise, satellite | R _L = 8 Ω, P _O = 10 W | | .1 | | % |
| | | R _L = 8 Ω, 1 W | | .05 | | |
| | Total harmonic distortion + noise, subwoofer | R _L = 4 Ω, P _O = 20 W | | .1 | | |
| | | R _L = 4 Ω, 1 W | | .05 | | |
| V _n | Output integrated noise, satellite | A-weighted | | 55 | | μV |
| | Output integrated noise, subwoofer | A-weighted | | 60 | | |
| SNR | System signal-to-noise ratio | A-weighted | | 105 | | dB |
| DNR | Dynamic range ⁽¹⁾ | A-weighted, –60 dBFS input signal | | 105 | | dB |
| P _{idle} | Power dissipation due to idle losses (IPVDDX) | P _O = 0 W, all channels running 5.1 mode ⁽²⁾ | | 4.5 | | W |
| | | P _O = 0 W, 2.1 mode | | 2.2 | | W |

(1) SNR is calculated relative to 0-dBFS input level.

(2) Actual system idle losses are affected by core losses of output inductors.

AUDIO SPECIFICATION (BTL Operation)

PVDD_X = 24 V, GVDD = 12 V, audio frequency = 1 kHz, AES17 measurement filter, $F_{PWM} = 384$ kHz, case temperature = 75°C. Audio performance is recorded as a chipset, using TAS5086 PWM processor with an effective modulation index limit of 97%. All performance is in accordance with the foregoing specifications and recommended operating conditions unless otherwise specified.

| PARAMETER | | CONDITIONS | MIN | TYP | MAX | UNIT |
|--------------------|---|--|-----|-----|-----|------|
| P _{O,sat} | Power output per satellite channel | R _L = 8 Ω, 10% THD, clipped input signal | | 30 | | W |
| | | R _L = 8 Ω, 0 dBFS, unclipped input signal | | 20 | | |
| P _{O,sub} | Power output subwoofer channel | R _L = 6 Ω, 10% THD, clipped input signal | | 40 | | W |
| | | R _L = 6 Ω, 0 dBFS, unclipped input signal | | 30 | | |
| THD + N | Total harmonic distortion + noise | R _L = 8 Ω, P _O = 20 W | | .2 | | % |
| | | R _L = 8 Ω, 1 W | | .05 | | |
| | | R _L = 6 Ω, P _O = 30 W | | .2 | | |
| | | R _L = 6 Ω, 1 W | | .05 | | |
| V _n | Output integrated noise, satellite | A-weighted | | 60 | | μV |
| | Output integrated noise, subwoofer | A-weighted | | 65 | | |
| SNR | System signal-to-noise ratio | A-weighted | | 105 | | dB |
| DNR | Dynamic range ⁽¹⁾ | A-weighted, –60 dBFS input signal | | 105 | | dB |
| P _{idle} | Power dissipation due to idle losses (IPVDDX) | P _O = 0 W, all channels running 5.1 mode ⁽²⁾ | | 4.5 | | W |
| | | P _O = 0 W, 2.1 mode | | 2.2 | | W |

(1) SNR is calculated relative to 0-dBFS input level.

(2) Actual system idle losses are affected by core losses of output inductors.

ELECTRICAL CHARACTERISTICS

$F_{PWM} = 384$ kHz, $PVDD = 31$ V, $GVDD = 12$ V, $VDD = 12$ V, T_C (case temperature) = 25°C, unless otherwise noted. All performance is in accordance with recommended operating conditions, unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP | MAX | UNIT |
|---|--|--|------|-----|-----|---------|
| INTERNAL VOLTAGE REGULATOR AND CURRENT CONSUMPTION | | | | | | |
| VREG | Voltage regulator, only used as reference node | VDD = 12 V | 3 | 3.3 | 3.6 | V |
| IVDD | VDD supply current | Operating, 50% duty cycle | | 7 | 20 | mA |
| | | Idle, reset mode | | 6 | 16 | |
| IGVDD_X | Gate supply current per half-bridge | 50% duty cycle | | 5 | 22 | mA |
| | | Idle, reset mode | | 1 | 3 | |
| IPVDD_X | Half-bridge idle current | 50% duty cycle, without output filter or load, 5.1 mode | | 180 | | mA |
| | | 50% duty cycle, without output filter or load, 2.1 mode | | 100 | | |
| OUTPUT STAGE MOSFETS | | | | | | |
| $R_{DS(on)}$, LS Sat | Drain-to-source resistance, low side, satellite | $T_J = 25^\circ\text{C}$, includes metallization resistance | | 210 | | mΩ |
| $R_{DS(on)}$, HS Sat | Drain-to-source resistance, high side, satellite | $T_J = 25^\circ\text{C}$, includes metallization resistance | | 210 | | mΩ |
| $R_{DS(on)}$, LS Sub | Drain-to-source resistance, low side, subwoofer | $T_J = 25^\circ\text{C}$, includes metallization resistance | | 110 | | mΩ |
| $R_{DS(on)}$, HS Sub | Drain-to-source resistance, high side, subwoofer | $T_J = 25^\circ\text{C}$, includes metallization resistance | | 110 | | mΩ |
| I/O PROTECTION | | | | | | |
| $V_{UVP, G}$ | Undervoltage protection limit GVDD_X | | | 10 | | V |
| $V_{UVP, hyst}^{(1)}$ | Undervoltage protection hysteresis | | | 250 | | mV |
| OTW ⁽¹⁾ | Overtemperature warning | | | 125 | | °C |
| OTW _{hyst} ⁽¹⁾ | Temperature drop needed below OTW temp. for OTW to be inactive after the OTW event | | | 25 | | °C |
| OTE ⁽¹⁾ | Overtemperature error | | | 155 | | °C |
| OTE _{HYST} ⁽¹⁾ | Temperature drop needed below OTE temp. for \overline{SD} to be released after the OTE event | | | 25 | | °C |
| OLCP | Overload protection counter | | 1.25 | | | ms |
| I_{OC} | Overcurrent limit protection, sat. | Resistor programmable, high end, R _{ocp} = 18 kΩ | | 4.5 | | A |
| | Overcurrent limit protection, sub. | Resistor programmable, high end, R _{ocp} = 18 kΩ | | 8 | | A |
| I_{OCT} | Overcurrent response time | | | 210 | | ns |
| R _{ocp} | OC programming resistor range | Resistor tolerance = 5% | | 27 | | kΩ |
| STATIC DIGITAL SPECIFICATION | | | | | | |
| V_{IH} | High-level input voltage | PWM_X, M1, M2, M3, RESET | | 2 | | V |
| V_{IL} | Low-level input voltage | | | | 0.8 | |
| I_{lkg} | Input leakage current | Static condition | -80 | | 80 | μA |
| OTW/SHUTDOWN (SD) | | | | | | |
| R_{INT_PU} | Internal pullup resistor to DREG (3.3 V) for \overline{SD} and OTW | | | 26 | | kΩ |
| V_{OH} | High-level output voltage | Internal pullup resistor only | 3 | 3.3 | 3.6 | V |
| | | External pullup: 4.7-kΩ resistor to 5 V | 4.5 | | 5 | |
| V_{OL} | Low-level output voltage | $I_O = 4$ mA | | 0.2 | 0.4 | |
| FANOUT | Device fanout \overline{OTW} , \overline{SD} | No external pullup | | 30 | | Devices |

(1) Specified by design.

TYPICAL CHARACTERISTICS, 5.1 MODE

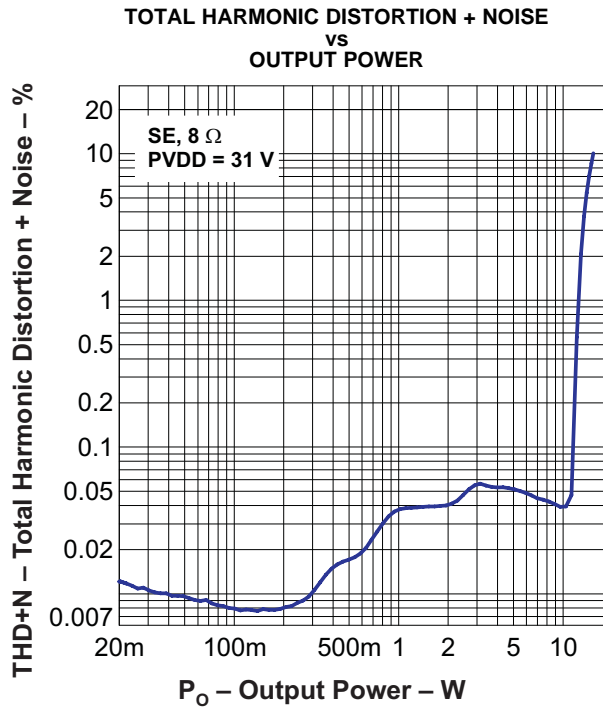


Figure 1.

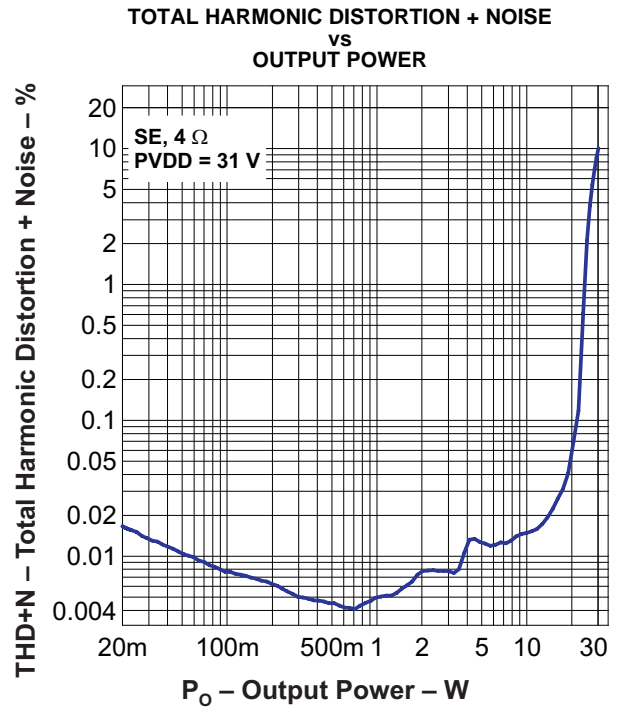


Figure 2.

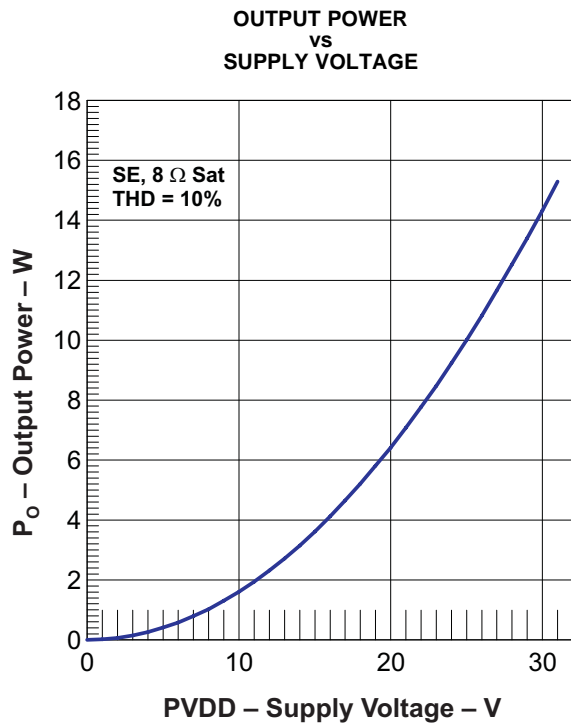


Figure 3.

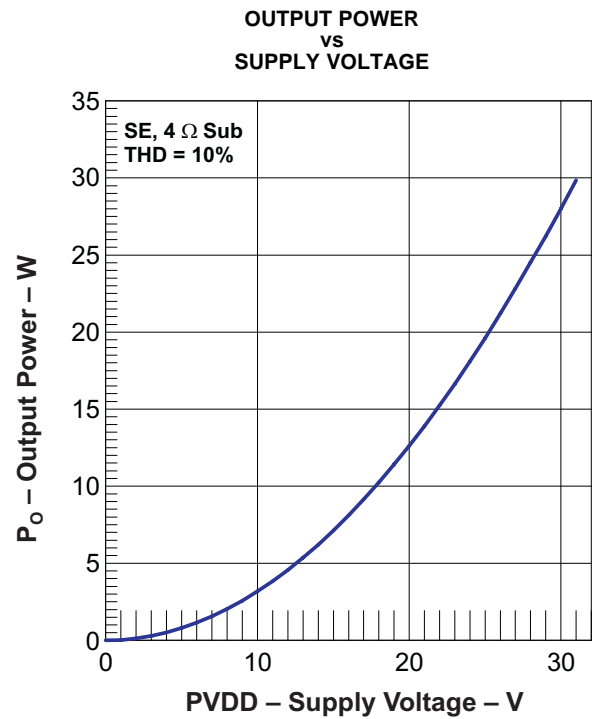


Figure 4.

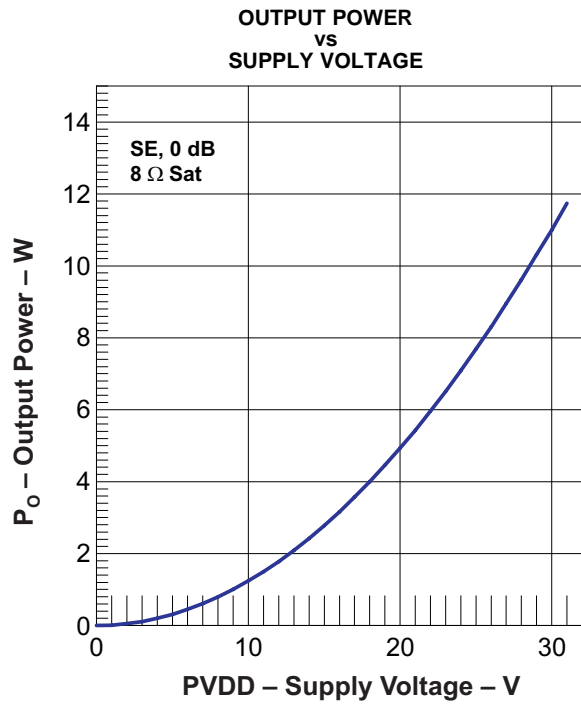


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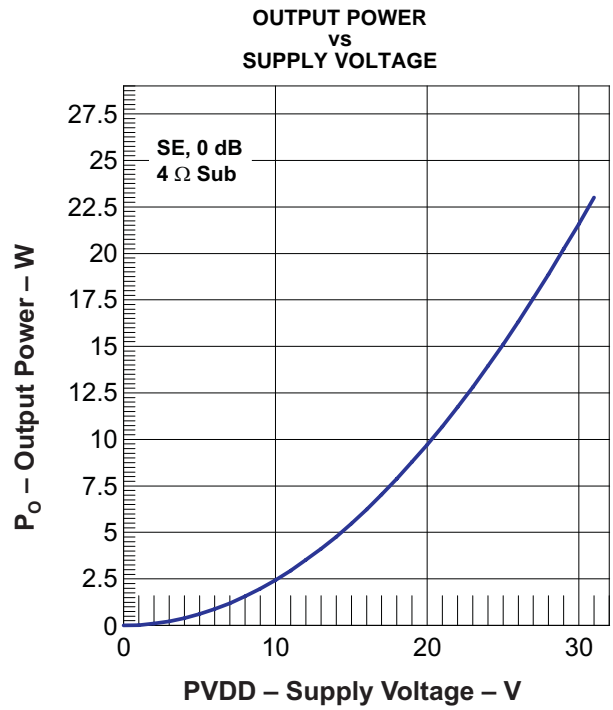


Figure 6.

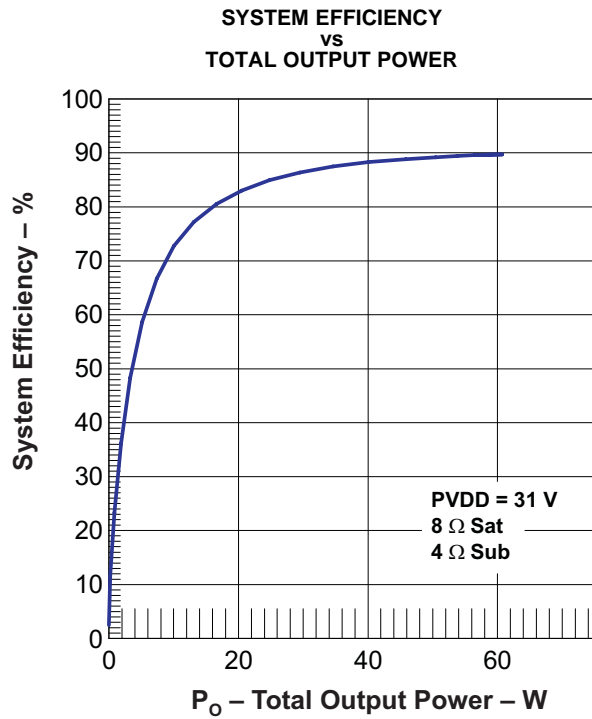


Figure 7.

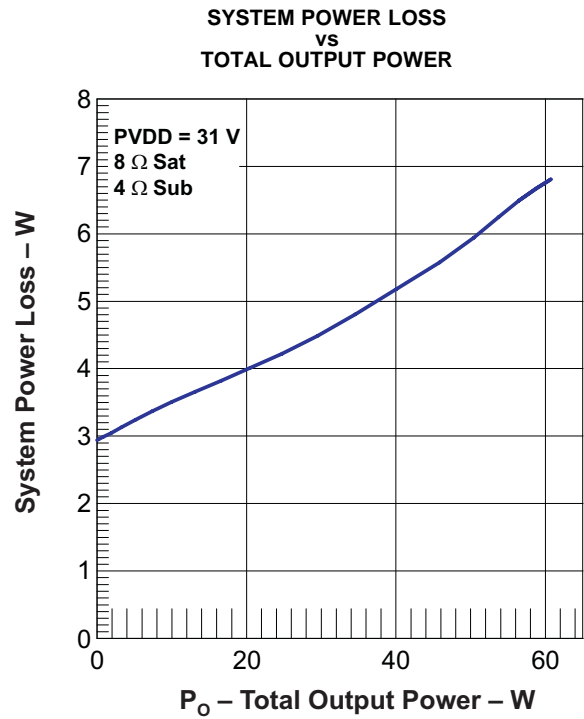


Figure 8.

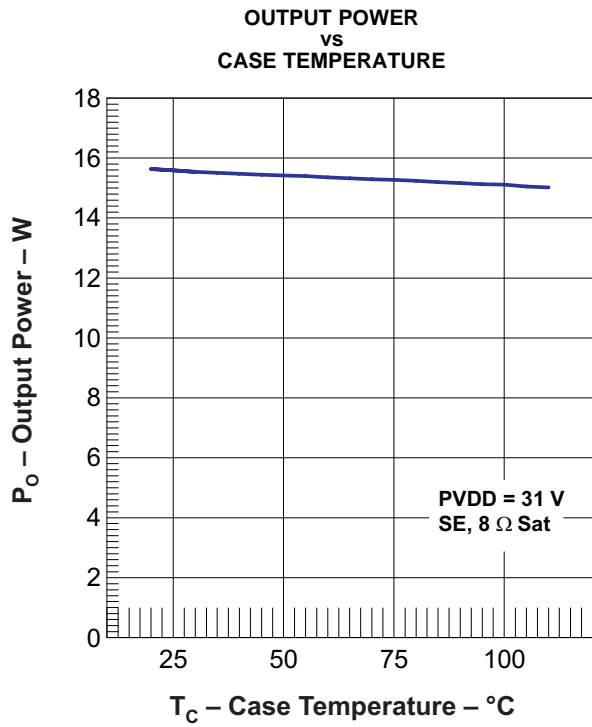


Figure 9.

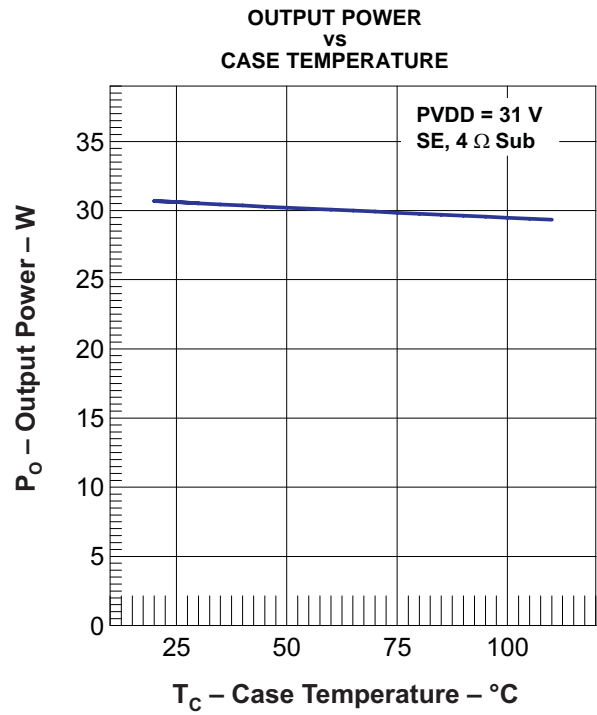


Figure 10.

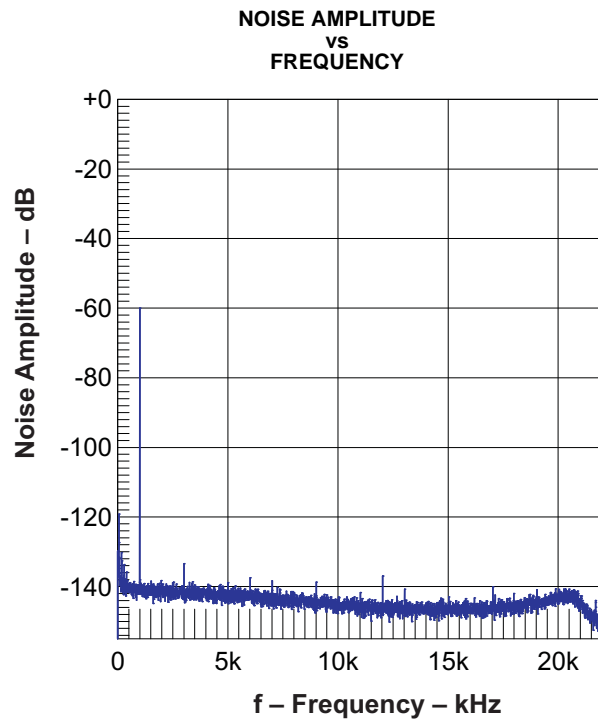
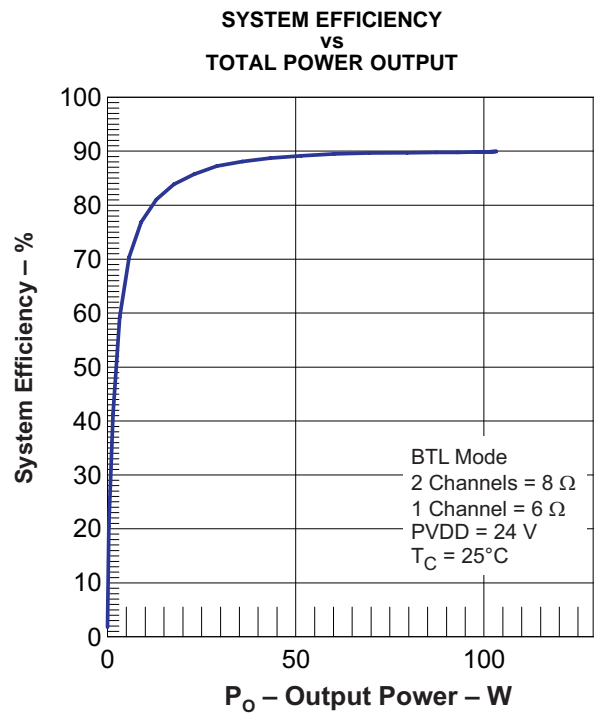
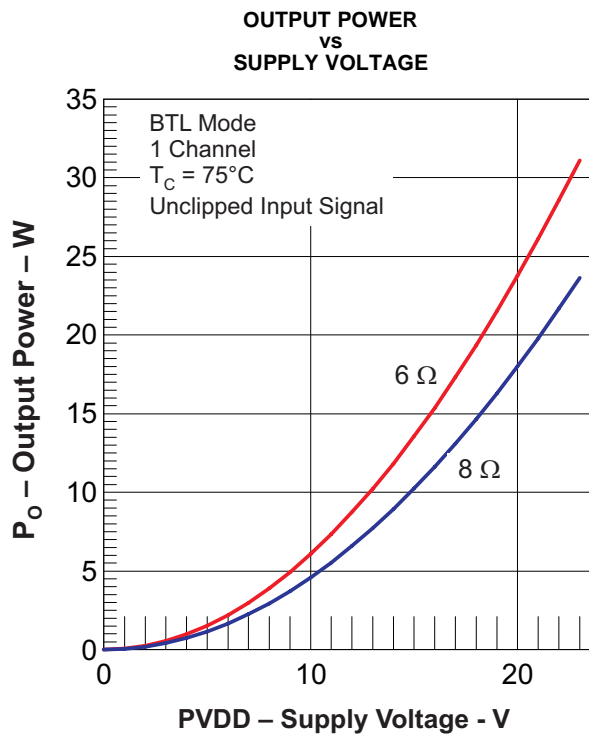
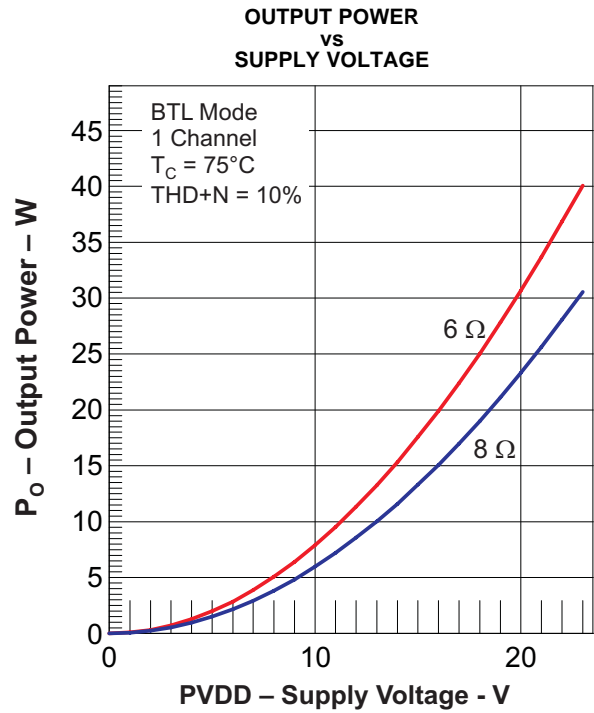
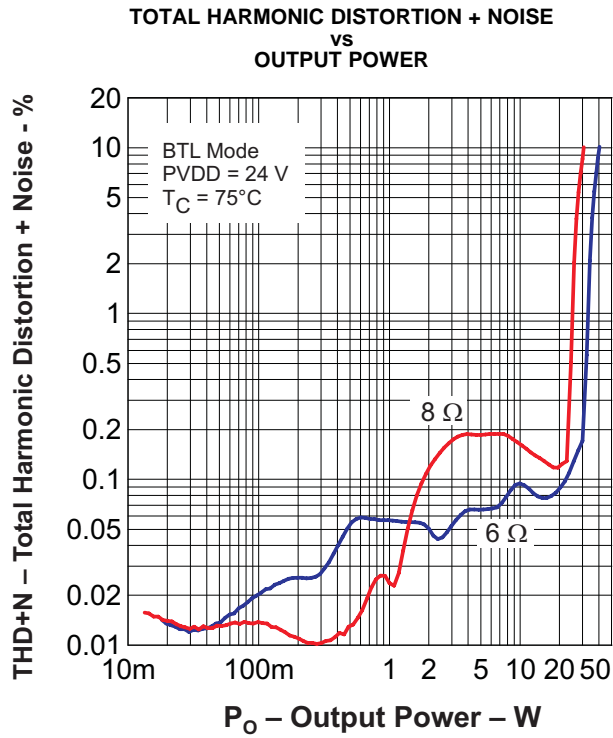


Figure 11.

TYPICAL CHARACTERISTICS, 3.0 BTL MODE



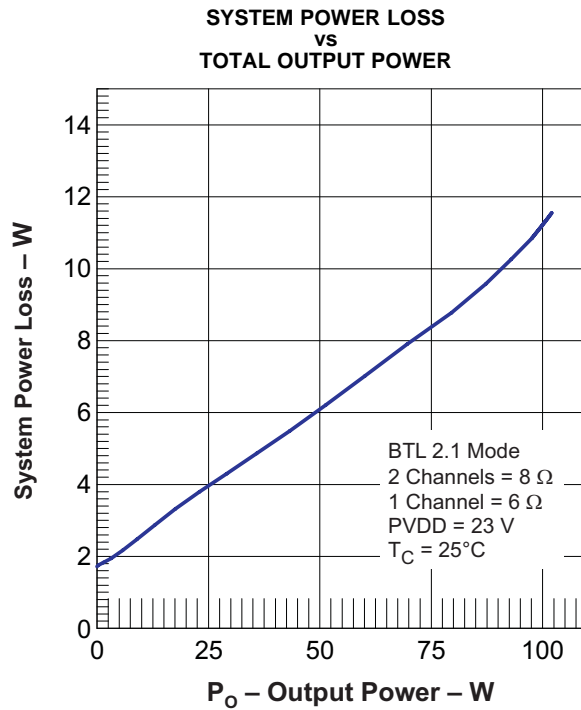


Figure 16.

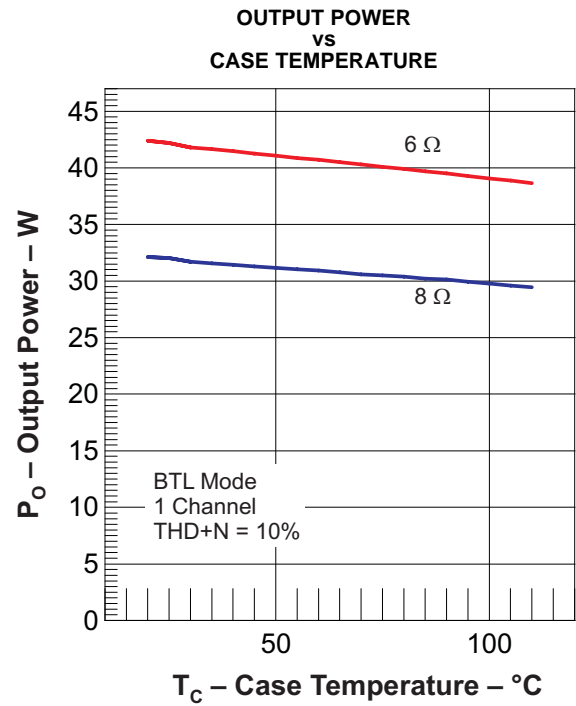


Figure 17.

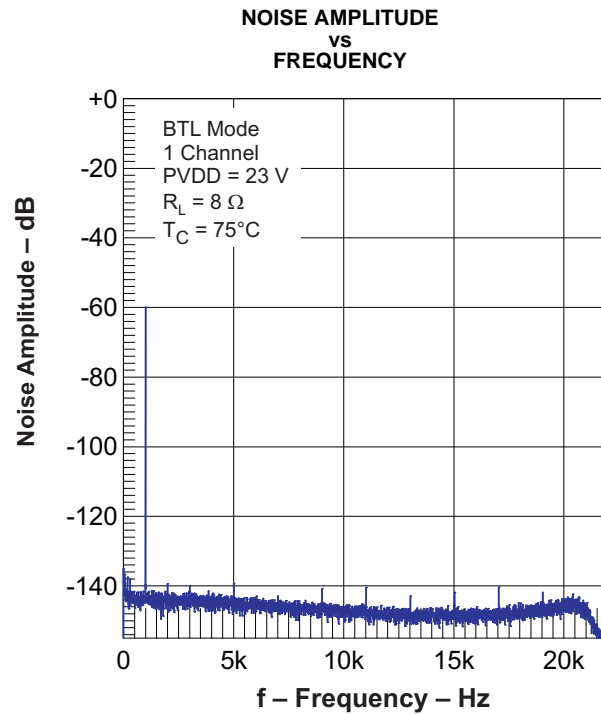


Figure 18.

THEORY OF OPERATION

POWER SUPPLIES

To facilitate system design, the TAS5176 needs only a 12-V supply in addition to a typical 31-V power-stage supply. An internal voltage regulator provides suitable voltage levels for the digital and low-voltage analog circuitry. Additionally, all circuitry requiring a floating voltage supply, e.g., the high-side gate drive, is accommodated by built-in bootstrap circuitry requiring only a few external capacitors.

In order to provide outstanding electrical and acoustic characteristics, the PWM signal path including gate drive and output stage is designed as identical, independent half-bridges. For this reason, each half-bridge has separate bootstrap pins (BST_X) and power-stage supply pins (PVDD_X). Furthermore, an additional pin (VDD) is provided as power supply for all common circuits. Although supplied from the same 12-V source, it is highly recommended to separate GVDD_X and VDD on the printed-circuit board (PCB) by RC filters (see application diagram for details). These RC filters provide the recommended high-frequency isolation. Special attention should be paid to placing all decoupling capacitors as close to their associated pins as possible. In general, inductance between the power-supply pins and decoupling capacitors must be avoided. (See reference board documentation for additional information.)

For a properly functioning bootstrap circuit, a small ceramic capacitor must be connected from each bootstrap pin (BST_X) to the power-stage output pin (OUT_X). When the power-stage output is low, the bootstrap capacitor is charged through an internal diode connected between the gate-drive power-supply pin (GVDD_X) and the bootstrap pin. When the power-stage output voltage is high, the bootstrap capacitor voltage is shifted above the output voltage potential and thus provides a suitable voltage supply for the high-side gate driver. In an application with PWM switching frequencies in the range 352 kHz to 384 kHz, it is recommended to use 33-nF ceramic capacitors, size 0603 or 0805, for the bootstrap capacitor. These 33-nF capacitors ensure sufficient energy storage, even during minimal PWM duty cycles, to keep the high-side power stage FET (LDMOS) fully started during all of the remaining part of the PWM cycle. In an application running at a reduced switching frequency, generally 250 kHz to 192 kHz, the bootstrap capacitor might need to be increased in value. Special attention should be paid to the power-stage power supply; this includes component selection, PCB placement and routing. As indicated, each half-bridge has independent power-stage supply pins (PVDD_X). For optimal electrical performance, EMI compliance, and system

reliability it is important that each PVDD_X pin is decoupled with a 100-nF ceramic capacitor placed as close as possible to each supply pin on the same side of the PCB as the TAS5176. It is recommended to follow the PCB layout and PowerPad layout of the TAS5176 reference design. For additional information on the recommended power supply and required components, see the application diagrams given in this data sheet. The 12-V supply should be powered from a low-noise, low-output-impedance voltage regulator. Likewise, the PVDD power-stage supply is assumed to have low output impedance and low noise. The power-supply sequence is not critical due to the internal power-on-reset circuit. Moreover, the TAS5176 is fully protected against erroneous power-stage turnon due to parasitic gate charging. Thus, voltage-supply ramp rates (dv/dt) are typically noncritical.

SYSTEM POWER-UP/DOWN SEQUENCE

The TAS5176 does not require a power-up sequence. The outputs of the H-bridge remain in a high-impedance state until the gate-drive supply voltage (GVDD_X) and VDD voltage are above the undervoltage protection (UVP) voltage threshold (see the *Electrical Characteristics* section of this data sheet). Although not specifically required, it is recommended to hold $\overline{\text{RESET}}$ in a low state while powering up the device.

When the TAS5176 is being used with TI PWM modulators such as the TAS5086, no special attention to the state of $\overline{\text{RESET}}$ is required, provided that the chipset is configured as recommended.

Powering Down

The TAS5176 does not require a power-down sequence. The device remains fully operational as long as the gate-drive supply (GVDD_X) voltage and VDD voltage are above the undervoltage protection (UVP) threshold level (see the *Electrical Characteristics* section of this data sheet). Although not specifically required, it is a good practice to hold $\overline{\text{RESET}}$ low during power down, thus preventing audible artifacts including pops and clicks.

When the TAS5176 is being used with TI PWM modulators such as the TAS5086, no special attention to the state of $\overline{\text{RESET}}$ is required, provided that the chipset is configured as recommended.

Error Reporting

The $\overline{\text{SD}}$ and $\overline{\text{OTW}}$ pins are both active-low, open-drain outputs. Their function is for protection-mode signaling to a PWM controller or other system-control device.

Any fault resulting in device shutdown is signaled by the \overline{SD} pin going low. Likewise, \overline{OTW} goes low when the device junction temperature exceeds 125°C (see the following table).

| \overline{SD} | \overline{OTW} | DESCRIPTION |
|-----------------|------------------|--|
| 0 | 0 | Overtemperature (OTE) or overload (OLP) or undervoltage (UVP) |
| 0 | 1 | Overload (OLP) or undervoltage (UVP) |
| 1 | 0 | Overtemperature warning. Junction temperature higher than 125°C, typical |
| 1 | 1 | Normal operation. Junction temperature lower than 125°C, typical |

It should be noted that asserting \overline{RESET} low forces the \overline{SD} and \overline{OTW} signals high independently of faults being present. It is recommended to monitor the \overline{OTW} signal using the system microcontroller and to respond to an overtemperature warning signal by, e.g., turning down the volume to prevent further heating of the device that would result in device shutdown (OTE). To reduce external component count, an internal pullup resistor to 3.3 V is provided on both the \overline{SD} and \overline{OTW} outputs. Level compliance for 5-V logic can be obtained by adding external pullup resistors to 5 V (see the *Electrical Characteristics* section of this data sheet for further specifications).

Device Protection System

The TAS5176 contains advanced protection circuitry carefully designed to facilitate system integration and ease of use, as well as safeguarding the device from permanent failure due to a wide range of fault conditions such as short circuit, overload, and undervoltage. The TAS5176 responds to a fault by immediately setting the power stage in a high-impedance state (Hi-Z) and asserting the \overline{SD} pin low. In situations other than overload, the device automatically recovers when the fault condition has been removed, e.g., the supply voltage has increased or the temperature has dropped. For highest possible reliability, recovering from an overload fault requires external reset of the device no sooner than 1 second after the shutdown (see the *Device Reset* section of this data sheet).

OVERCURRENT (OC) PROTECTION WITH CURRENT LIMITING AND OVERLOAD DETECTION

The device has independent, fast-reacting current detectors with programmable trip threshold (OC threshold) on all high-side and low-side power-stage FETs. See the following table for OC-adjust resistor values. The detector outputs are closely monitored by two protection systems. The first protection

system controls the power stage in order to prevent the output current from further increasing. I.e., it performs a current-limiting function rather than prematurely shutting down during combinations of high-level music transients and extreme speaker load-impedance drops. If the high-current situation persists, i.e., the power stage is being overloaded, a second protection system triggers a latching shutdown, resulting in the power stage being set in the high-impedance (Hi-Z) state.

For added flexibility, the OC threshold is programmable within a limited range using a single external resistor connected between the OC_ADJ pin and AGND.

| OC-Adjust Resistor Values (k Ω) | Maximum Current Before OC Occurs (A) |
|---|--------------------------------------|
| 18K | 4.5 (sat), 8.0 (sub) |
| 27K | TBD |

It should be noted that a properly functioning overcurrent detector assumes the presence of a properly designed demodulation filter at the power-stage output. Short-circuit protection is not provided directly at the output pins of the power stage but only on the speaker terminals (after the demodulation filter). It is required to follow certain guidelines when selecting the OC threshold and an appropriate demodulation inductor.

- For the lowest-cost bill of materials in terms of component selection, the OC threshold current should be limited, considering the power output requirement and minimum load impedance. Higher-impedance loads require a lower OC threshold.
- The demodulation filter inductor must retain at least 5 μ H of inductance at twice the OC threshold setting.

Most inductors have decreasing inductance with increasing temperature and increasing current (saturation). To some degree, an increase in temperature naturally occurs when operating at high output currents, due to inductor core losses and the dc resistance of the inductor copper winding. A thorough analysis of inductor saturation and thermal properties is strongly recommended.

Setting the OC threshold too low might cause issues such as lack of output power and/or unexpected shutdowns due to sensitive overload detection.

In general, it is recommended to follow closely the external component selection and PCB layout as given in the application section.

OVERTEMPERATURE PROTECTION

The TAS5176 has a two-level temperature-protection system that asserts an active-low warning signal (\overline{OTW}) when the device junction temperature exceeds 125°C (typical), and if the device junction temperature exceeds 155°C (typical), the device is put into thermal shutdown, resulting in all half-bridge outputs being set in the high-impedance state (Hi-Z) and \overline{SD} being asserted low.

THERMAL CONSIDERATIONS

The TAS5176 device package (DDW) is designed with the PowerPad on the bottom of the device. It must be soldered to the ground plane on the printed circuit board (PCB). Under the PowerPad, there should be a pattern of vias to conduct heat through the PCB to the bottom layer ground plane. Using this technique alone, the device is capable of a total continuous power of 80 Watts.

Additional heatsinking is required for total continuous power of 100 Watts. An exposed area in the bottom layer soldermask can be created and then an aluminum bracket mechanically and thermally coupled (with heatsink paste) to the exposed area. The other end of the aluminum bracket can then be mechanically and thermally connected to the system chassis. This technique will allow the TAS5176 to run at higher ambient temperatures and/or deliver more power.

UNDERVOLTAGE PROTECTION (UVP) AND POWER-ON RESET (POR)

The UVP and POR circuits of the TAS5176 fully protect the device in any power-up/down and brownout situation. While powering up, the POR circuit resets the overload circuit (OLP) and ensures that all circuits are fully operational when the GVDD_X and VDD supply voltages reach 10 V (typical). Although GVDD_X and VDD are independently monitored, a supply voltage drop below the UVP threshold on any VDD or GVDD_X pin results in all half-bridge outputs immediately being set in the high-impedance (Hi-Z) state and \overline{SD} being asserted low. The device automatically resumes operation when all supply voltages have increased above the UVP threshold.

DEVICE RESET

When \overline{RESET} is asserted low, the output FETs in all half-bridges are forced into a high-impedance (Hi-Z) state.

Asserting the \overline{RESET} input low removes any fault information to be signaled on the \overline{SD} output, i.e., \overline{SD} is forced high.

A rising-edge transition on the \overline{RESET} input allows the device to resume operation after an overload fault.

ACTIVE-BIAS CONTROL (ABC)

Audible pop noises are often associated with single-rail, single-ended power stages at power-up or at the start of switching. This commonly known problem has been virtually eliminated by incorporating a proprietary active-bias control circuitry as part of the TAS5176 feature set. By the use of only a few passive external components (typically resistors), the ABC can pre-charge the dc-blocking element in the audio path, i.e., split-cap capacitors or series capacitor, to the desired potential before switching is started on the PWM outputs. (For recommended configuration, see the typical application schematic included in this data sheet).

The start-up sequence can be controlled through sequencing the M3 and \overline{RESET} pins according to [Table 2](#) and [Table 3](#).

Table 2. 5.1 Mode—All Output Channels Active

| M3 | \overline{RESET} | OUT_BIAS | OUT_A, _B, _C | OUT_D, _E, _F | COMMENT |
|----|--------------------|----------|---------------|---------------|--|
| 0 | 0 | Hi-Z | Hi-Z | Hi-Z | All outputs disabled, nothing is switching. |
| 1 | 0 | Active | Hi-Z | Hi-Z | OUT_BIAS enabled, all other outputs disabled |
| 1 | 1 | Hi-Z | Active | Active | OUT_BIAS disabled, all other outputs switching |

Table 3. 2.1 Mode—Only Output Channels A, B, and C Active

| M3 | \overline{RESET} | OUT_BIAS | OUT_A, _B, _C | OUT_D, _E, _F | COMMENT |
|----|--------------------|----------|---------------|---------------|--|
| 0 | 0 | Hi-Z | Hi-Z | Hi-Z | All outputs disabled, nothing is switching. |
| 1 | 0 | Active | Hi-Z | Hi-Z | OUT_BIAS enabled, all other outputs disabled |
| 0 | 1 | Hi-Z | Active | Hi-Z | OUT_BIAS disabled, all other outputs switching |

Table 4. 3.0 Mode—Output Channels In BTL Mode

| M3 | RESET | OUT_BIAS | OUT_A, _B, _C | OUT_D, _E, _F | COMMENT |
|----|-------|----------|------------------|------------------|---|
| 0 | 0 | Hi-Z | Hi-Z | Hi-Z | All outputs disabled, nothing is switching. |

| M3 | RESET | OUT_BIAS | OUT_A, _B, _C | OUT_D, _E, _F | COMMENT |
|----|-------|----------|------------------|------------------|--|
| 1 | 0 | Active | Hi-Z | Hi-Z | OUT_BIAS enabled, all other outputs disabled |
| 0 | 1 | Hi-Z | Active | Hi-Z | OUT_BIAS disabled, all other outputs switching |

When the TAS5176 is used with the TAS5086 PWM modulator, no special attention to start-up sequencing is required, provided that the chipset is configured as recommended.

PACKAGING INFORMATION

| Orderable Device | Status (1) | Package Type | Package Drawing | Pins | Package Qty | Eco Plan (2) | Lead finish/ Ball material (6) | MSL Peak Temp (3) | Op Temp (°C) | Device Marking (4/5) | Samples |
|------------------|---------------|--------------|-----------------|------|-------------|-----------------|--------------------------------------|----------------------|--------------|-------------------------|---------|
| TAS5176DDW | ACTIVE | HTSSOP | DDW | 44 | 35 | RoHS & Green | NIPDAU | Level-3-260C-168 HR | 0 to 70 | TAS5176 | Samples |

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "-" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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TUBE


*All dimensions are nominal

| Device | Package Name | Package Type | Pins | SPQ | L (mm) | W (mm) | T (μm) | B (mm) |
|------------|--------------|--------------|------|-----|--------|--------|--------|--------|
| TAS5176DDW | DDW | HTSSOP | 44 | 35 | 530 | 11.89 | 3600 | 4.9 |

GENERIC PACKAGE VIEW

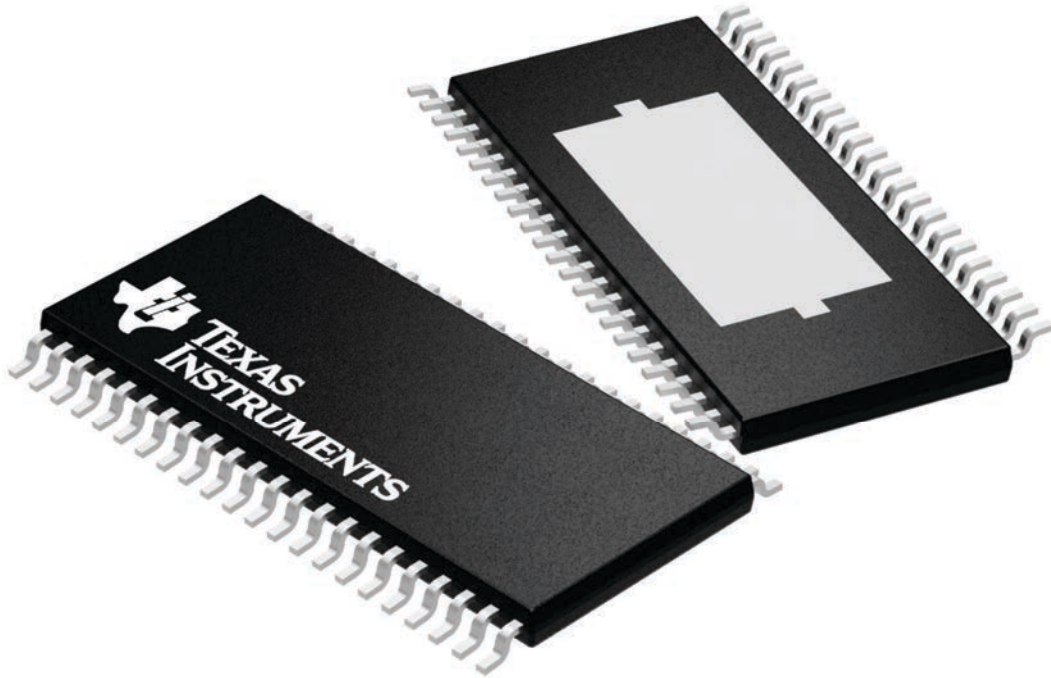
DDW 44

PowerPAD TSSOP - 1.2 mm max height

6.1 x 14, 0.635 mm pitch

PLASTIC SMALL OUTLINE

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

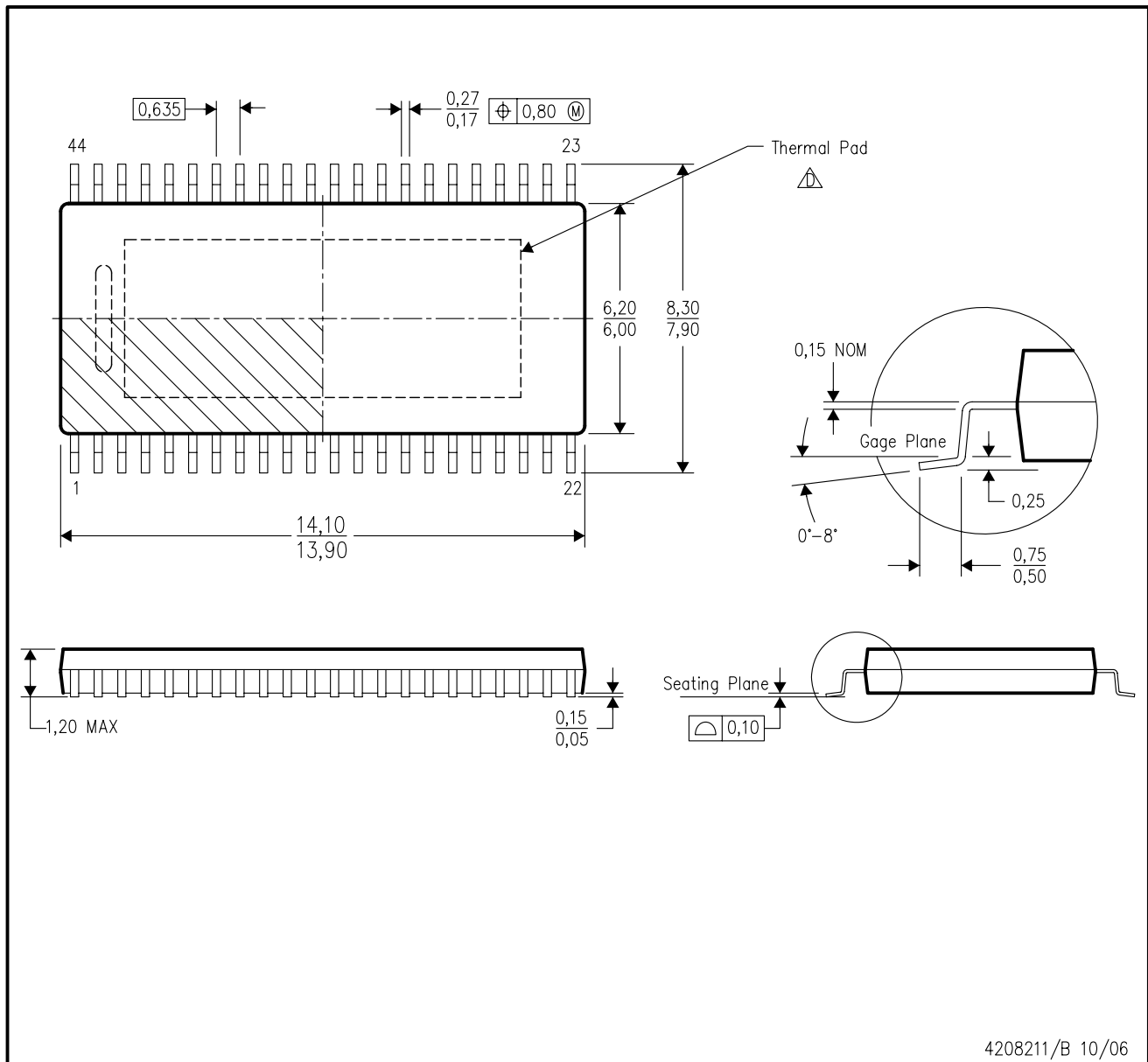


4224876/A

MECHANICAL DATA

DDW (R-PDSO-G44)

PowerPAD™ PLASTIC SMALL-OUTLINE PACKAGE (PAD DOWN)



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.
 - △ This package thermal performance is optimized for conductive cooling with attachment to an external heat sink. See the product data sheet for details regarding the exposed thermal pad dimensions.

PowerPAD is a trademark of Texas Instruments.

THERMAL PAD MECHANICAL DATA

DDW (R-PDSO-G44)

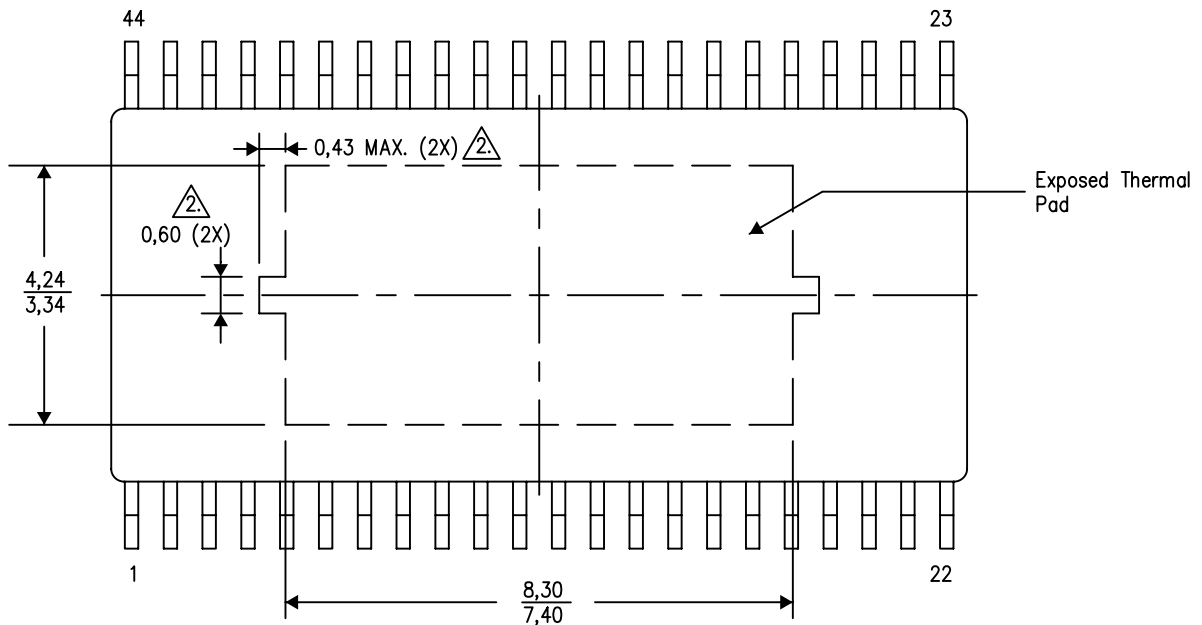
PowerPAD™ SMALL OUTLINE PACKAGE

THERMAL INFORMATION

This PowerPAD™ package incorporates an exposed thermal pad that is designed to be attached to a printed circuit board (PCB). The thermal pad must be soldered directly to the PCB. After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For additional information on the PowerPAD package and how to take advantage of its heat dissipating abilities, refer to Technical Brief, PowerPAD Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 and Application Brief, PowerPAD Made Easy, Texas Instruments Literature No. SLMA004. Both documents are available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



Top View

1. All linear dimensions are in millimeters
2. These features may not be present.

Exposed Thermal Pad Dimensions

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